

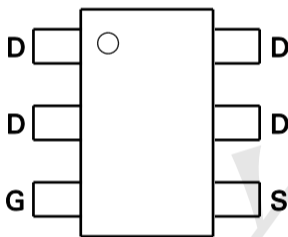
Product Summary

- -60V/-3A
 $R_{DS(ON)} = 95m\Omega (Typ) @ V_{GS} = -10V$
 $R_{DS(ON)} = 130m\Omega (Typ) @ V_{GS} = -4.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

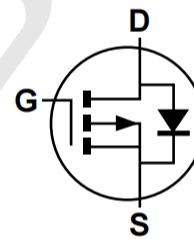
Application

- DC-DC Converters.
- Load Switch.
- Power Management.

Package and Pin Configuration



Circuit diagram



Equivalent Circuit

Marking: P 603P

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	-60	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	$V_{GS} = -10V$	(Note 6)	-3	A	
		$T_A = +70^\circ C$ (Note 6)	-2.4		
		(Note 5)	-2.3		
Pulsed Drain Current	$V_{GS} = -10V$	(Note 7)	I_{DM}	-13.6	A
Continuous Source Current (Body Diode)		(Note 6)	I_S	-2.5	A
Pulsed Source Current (Body Diode)		(Note 7)	I_{SM}	-13.6	A

Thermal Characteristics (@ $T_A = +25^\circ C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor	(Note 5)	P_D	1.1	W
	(Note 6)		8.8	
	(Note 6)		15.4	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	113	$^\circ C/W$
	(Note 6)		65	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ C$



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SI3459BDV

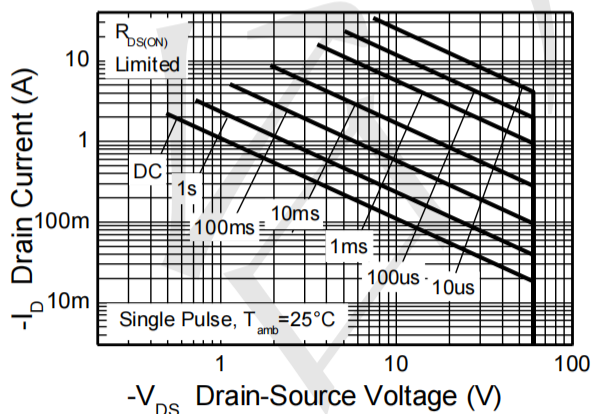
60V P-CHANNEL ENHANCEMENT MODE MOSFET

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

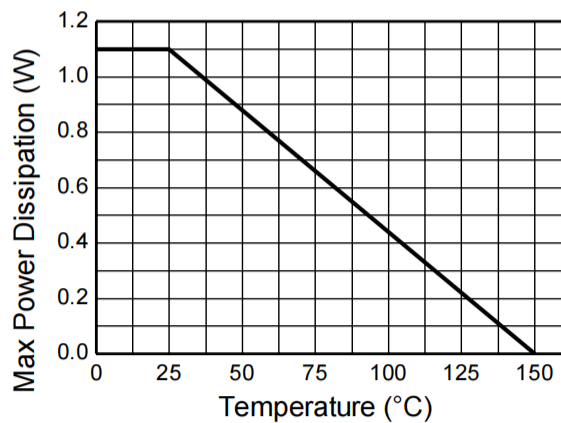
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Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	-60	—	—	V	$I_D = -250\mu\text{A}$, $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	μA	$V_{DS} = -48\text{V}$, $V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	-1	-1.5	-3	V	$I_D = -250\mu\text{A}$, $V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 8)	$R_{DS(on)}$	—	95	118	m Ω	$V_{GS} = -10\text{V}$, $I_D = -3\text{A}$
			130	190		$V_{GS} = -4.5\text{V}$, $I_D = -1.9\text{A}$
Forward Transconductance (Notes 8 & 9)	g_{fs}	—	4.7	—	S	$V_{DS} = -15\text{V}$, $I_D = -2.3\text{A}$
Diode Forward Voltage (Note 8)	V_{SD}	—	-0.85	-0.95	V	$I_S = -2\text{A}$, $V_{GS} = 0\text{V}$
Reverse Recovery Time (Note 9)	t_{rr}	—	25.1	—	ns	$I_F = -1.7\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge (Note 9)	Q_{rr}	—	27.2	—	nC	
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	637	—	pF	$V_{DS} = -30\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	70	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	53	—	pF	
Total Gate Charge (Note 10)	Q_g	—	9.8	—	nC	$V_{GS} = -5\text{V}$
Total Gate Charge (Note 10)	Q_g	—	17.7	—	nC	
Gate-Source Charge (Note 10)	Q_{gs}	—	1.6	—	nC	$V_{GS} = -10\text{V}$
Gate-Drain Charge (Note 10)	Q_{gd}	—	4.4	—	nC	
Turn-On Delay Time (Note 10)	$t_{D(on)}$	—	2.6	—	ns	$V_{DD} = -30\text{V}$, $V_{GS} = -10\text{V}$ $I_D = -1\text{A}$, $R_G \cong 6\Omega$
Turn-On Rise Time (Note 10)	t_r	—	3.4	—	ns	
Turn-Off Delay Time (Note 10)	$t_{D(off)}$	—	26.2	—	ns	
Turn-Off Fall Time (Note 10)	t_f	—	11.3	—	ns	

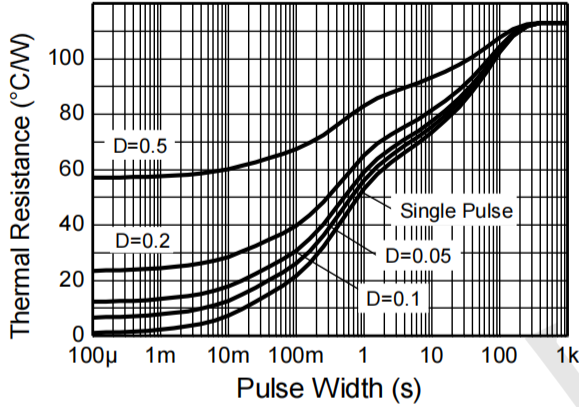
Typical Performance Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise Specified)



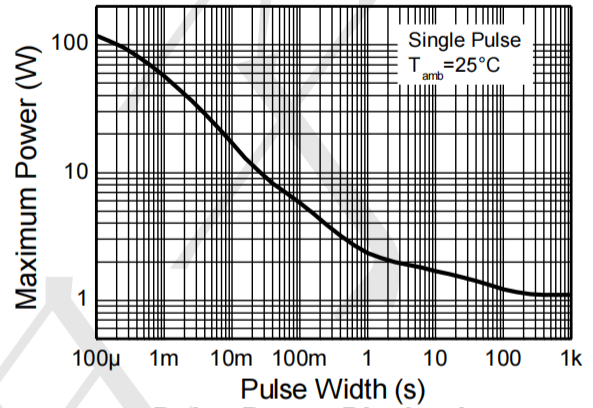
P-channel Safe Operating Area



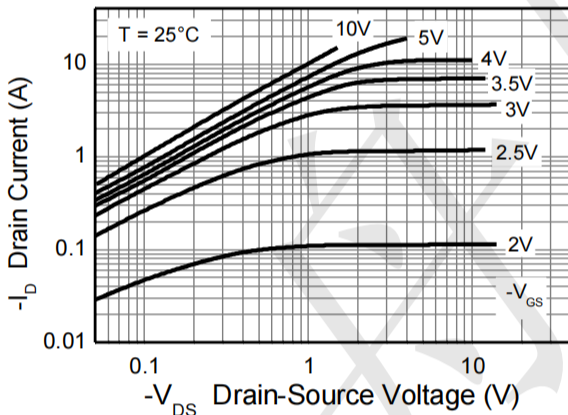
Derating Curve



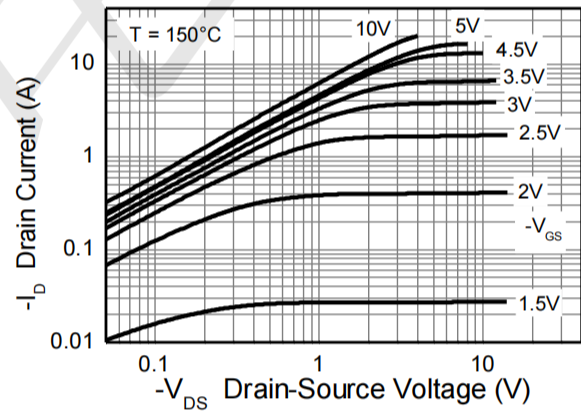
Transient Thermal Impedance



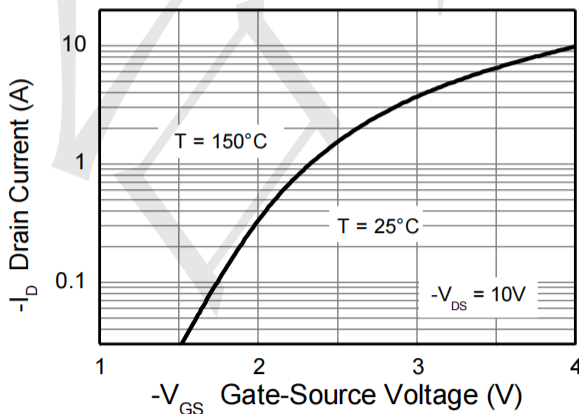
Pulse Power Dissipation



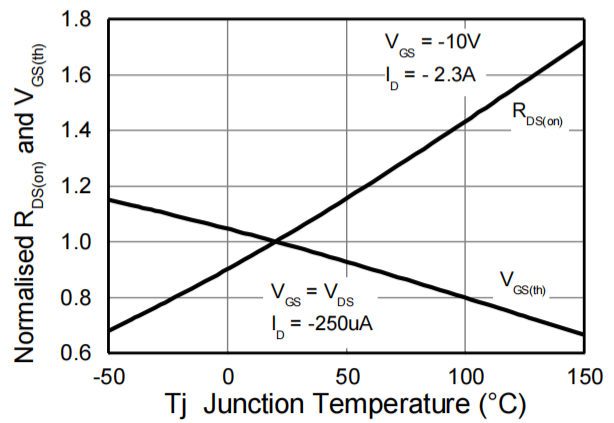
Output Characteristics



Output Characteristics



Typical Transfer Characteristics



Normalised Curves v Temperature



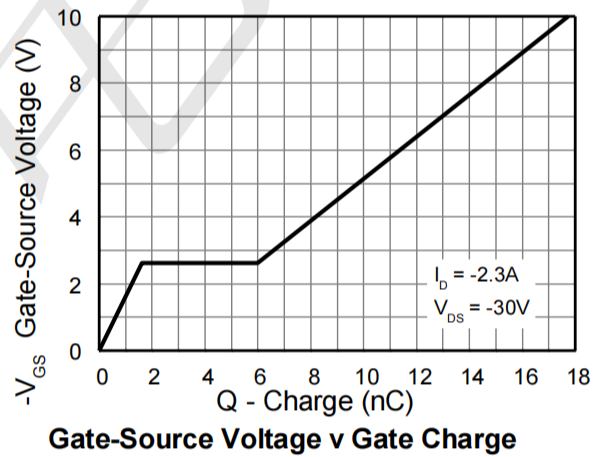
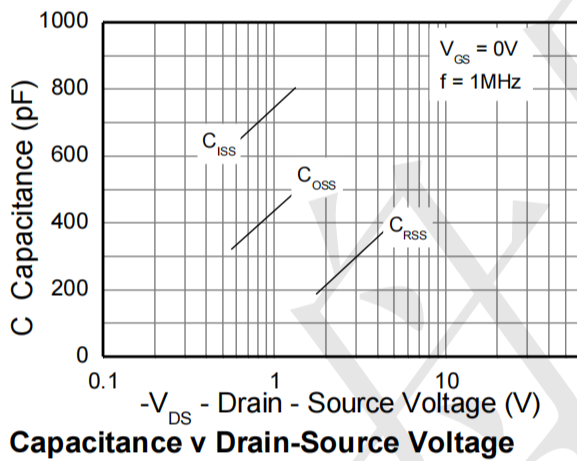
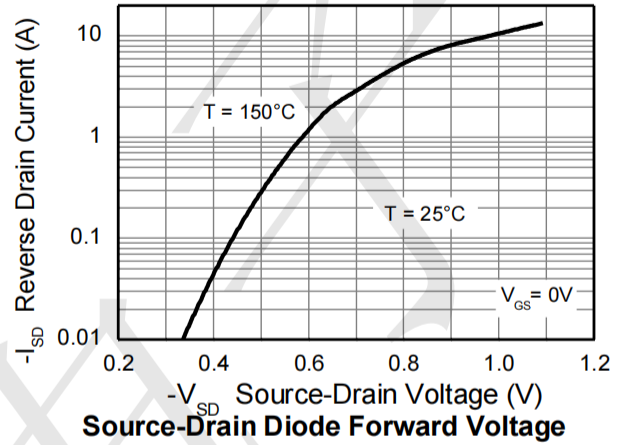
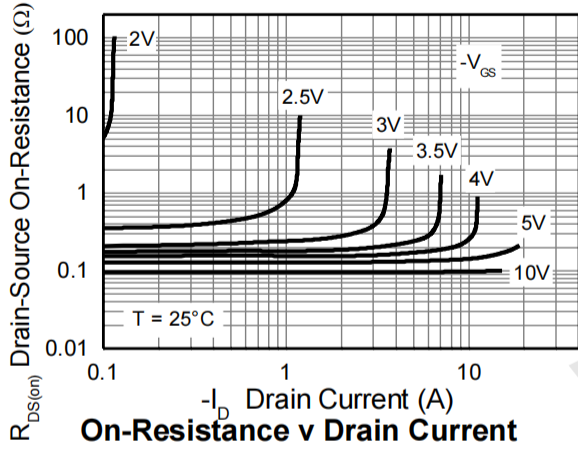
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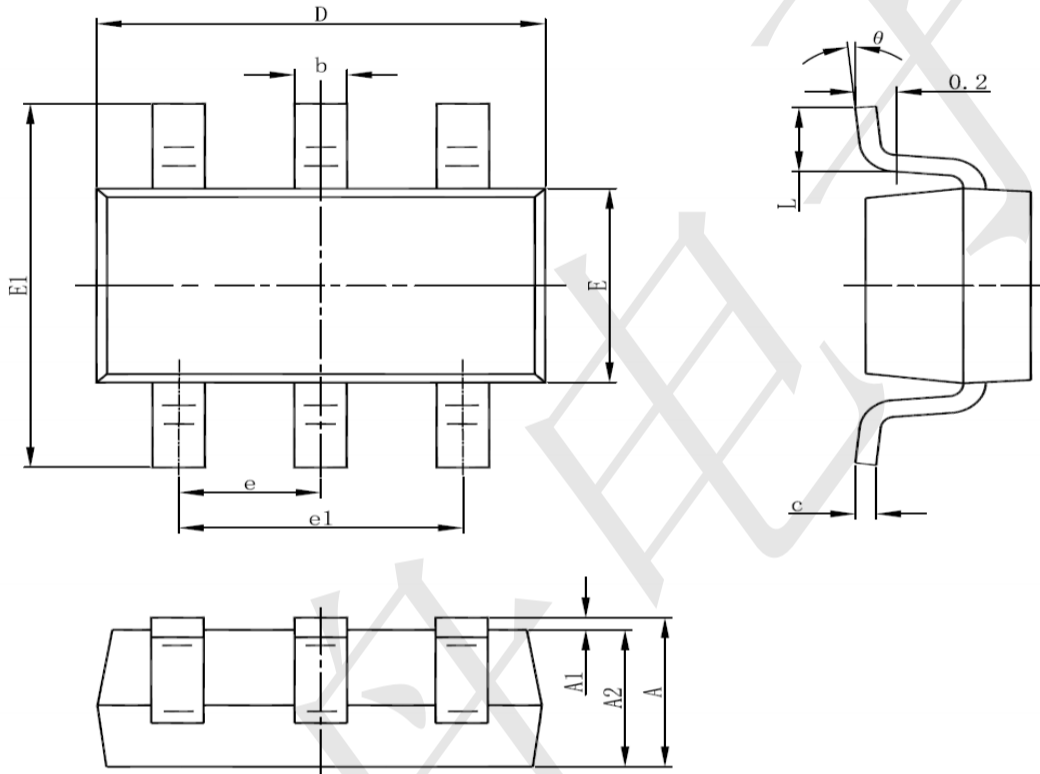
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SOT23-6 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°